

## NPN General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1.0 A. Sourced from Process 39.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	80	V
V <sub>CBO</sub>	Collector-Base Voltage	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	1.2	A
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max Unit		Units
		TN6717A	*NZT6717	
P <sub>D</sub>	Total Device Dissipation	1.0	1.0	W
	Derate above 25°C	8.0	8.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	50		°C/W
$R_{ ext{ hetaJA}}$	Thermal Resistance, Junction to Ambient	125	125	°C/W

\*Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm<sup>2</sup>.

## **NPN General Purpose Amplifier** (c

continued)	

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAF	RACTERISTICS				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	80		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = 100 \ \mu A, \ I_{E} = 0$	80		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 100 \ \mu A, \ I_C = 0$	5.0		V
I <sub>CBO</sub>	Collector-Cutoff Current	$V_{CB} = 60 \text{ V}, \text{ I}_{E} = 0$		0.1	μA
I <sub>EBO</sub>	Emitter-Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$		0.1	μA

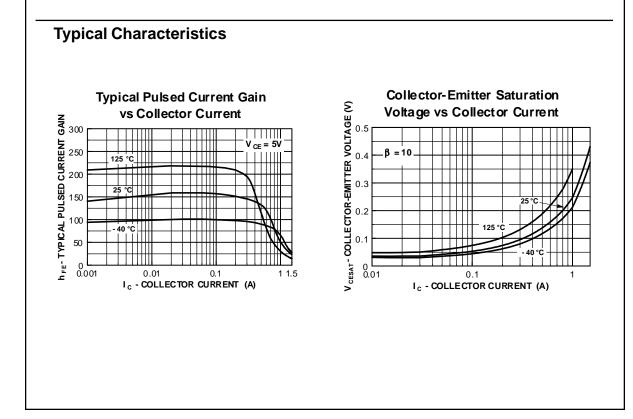
1ARACTERISTICS

h <sub>FE</sub>	DC Current Gain	$    I_C = 50 \text{ mA}, V_{CE} = 1.0 \text{ V} \\     I_C = 250 \text{ mA}, V_{CE} = 1.0 \text{ V} \\     I_C = 500 \text{ mA}, V_{CE} = 1.0 \text{ V} $	80 50 20	250	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{\rm C} = 250 \text{ mA}, I_{\rm B} = 10 \text{ mA}$		0.35	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_{C} = 250 \text{ mA}, V_{CE} = 1.0 \text{ V}$		1.2	V

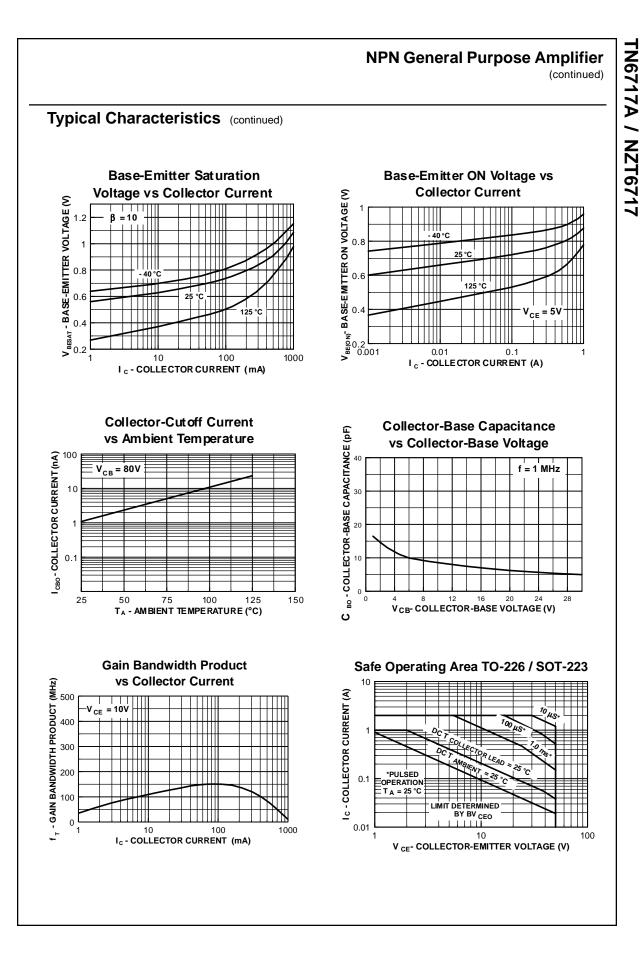
### SMALL SIGNAL CHARACTERISTICS

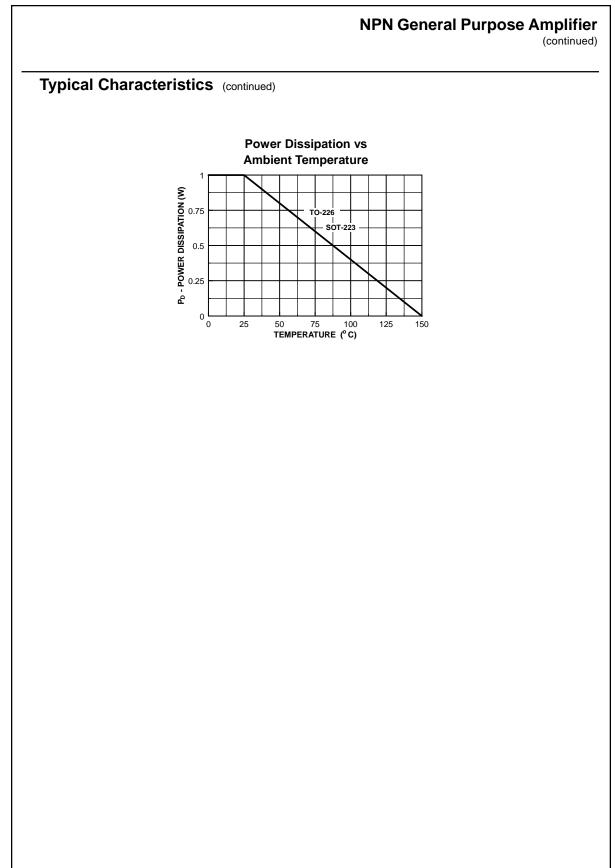
h <sub>fe</sub>	Small-Signal Current Gain	$I_{C} = 200 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 20 MHz	2.5	25	
C <sub>cb</sub>	Collector-Base Capacitance	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz		30	pF

\*Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  1.0%

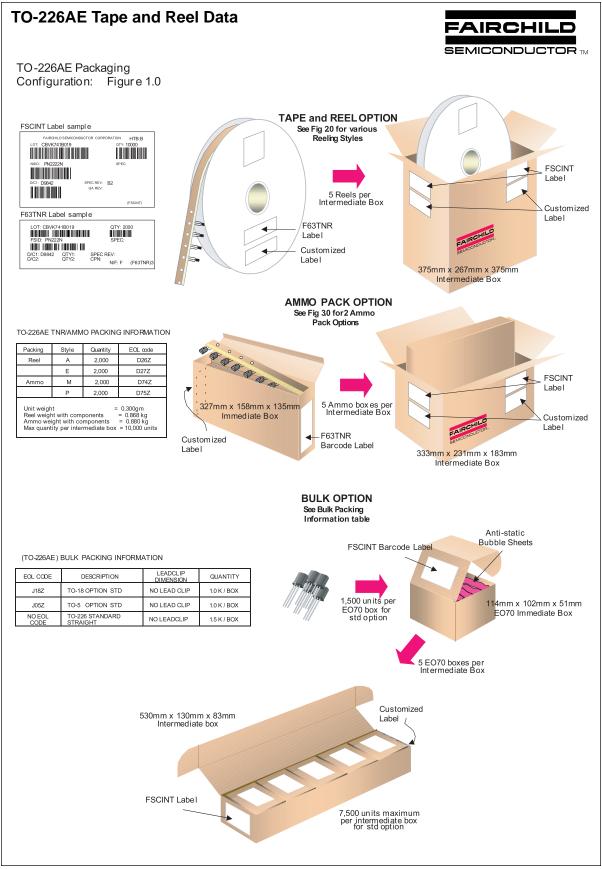


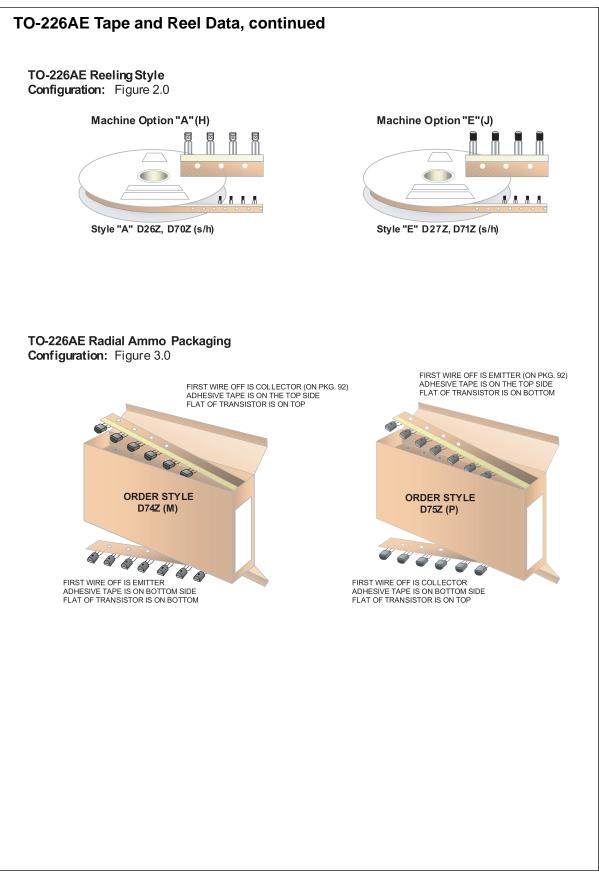
TN6717A / NZT6717

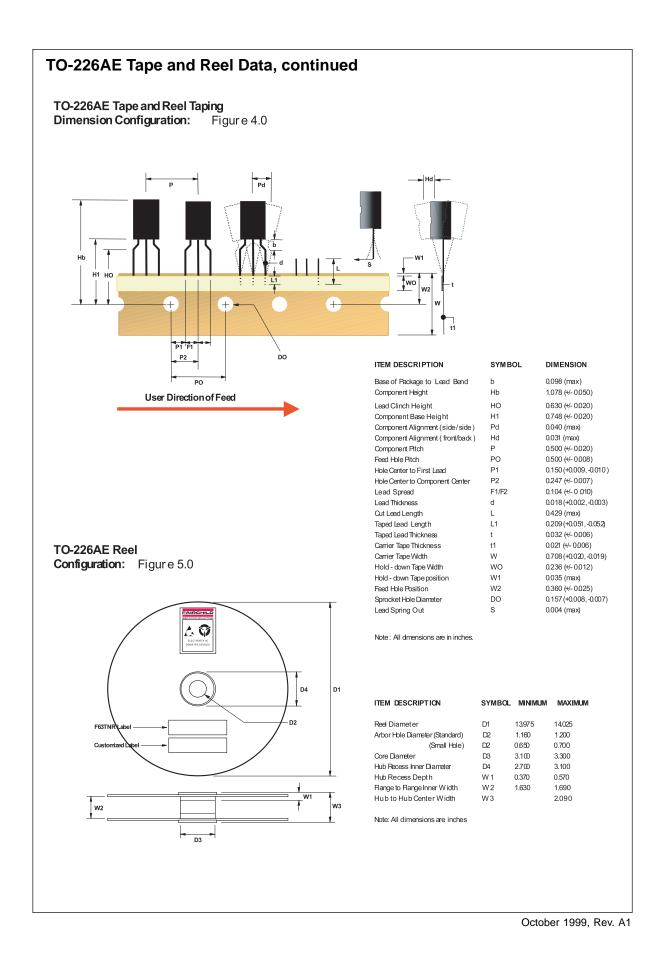


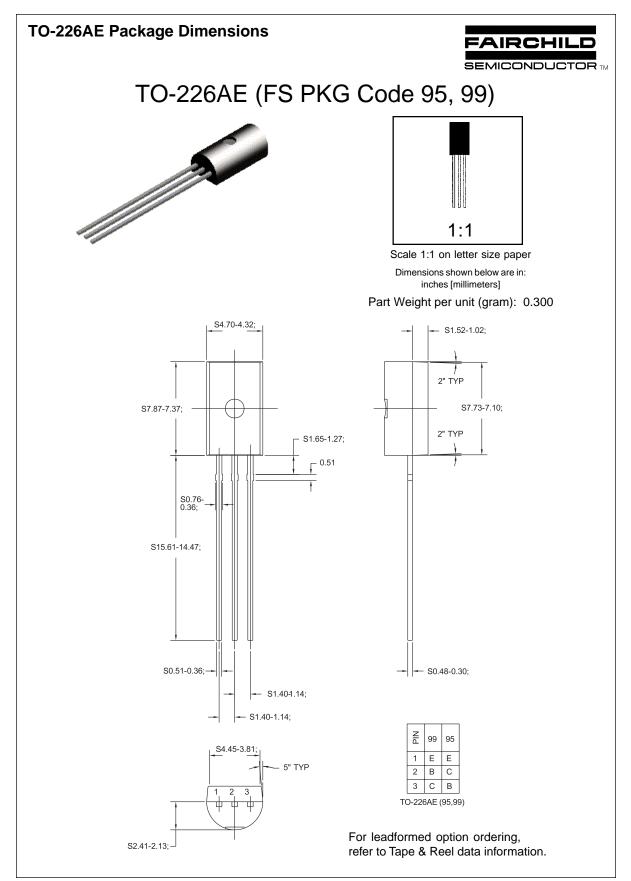


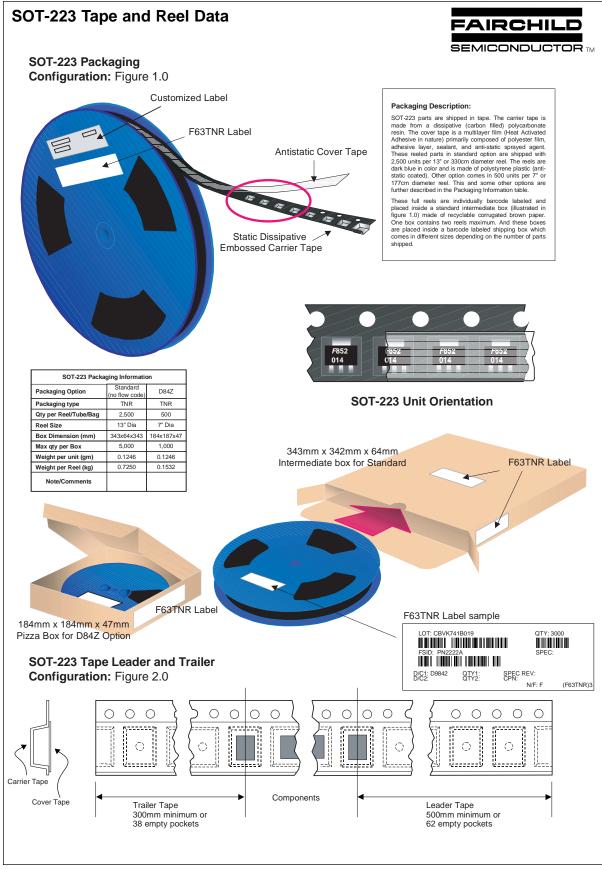
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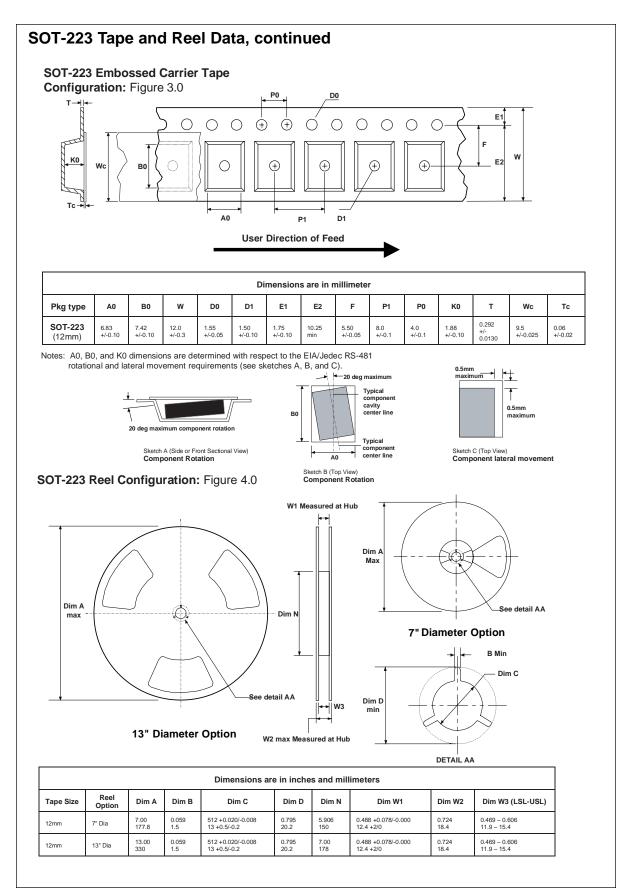


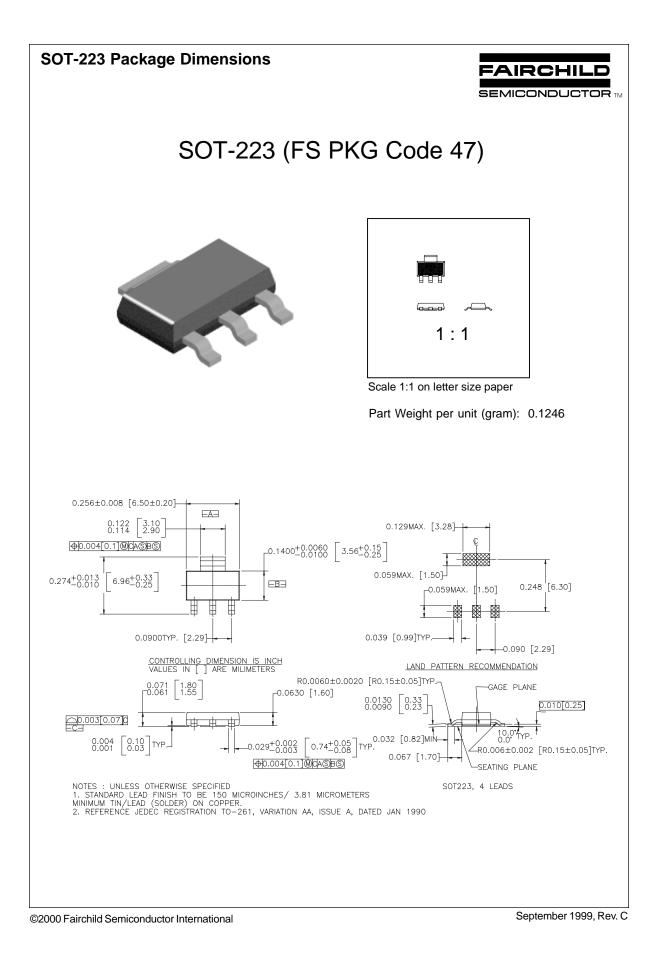




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